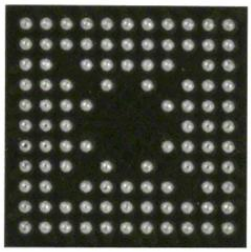

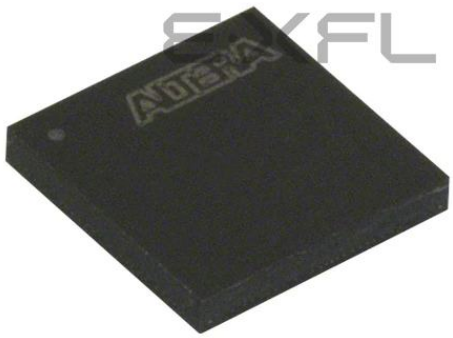

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Understanding Embedded - CPLDs (Complex Programmable Logic Devices)

Embedded - CPLDs, or Complex Programmable Logic Devices, are highly versatile digital logic devices used in electronic systems. These programmable components are designed to perform complex logical operations and can be customized for specific applications. Unlike fixed-function ICs, CPLDs offer the flexibility to reprogram their configuration, making them an ideal choice for various embedded systems. They consist of a set of logic gates and programmable interconnects, allowing designers to implement complex logic circuits without needing custom hardware.

Applications of Embedded - CPLDs

Details	
Product Status	Active
Programmable Type	In System Programmable
Delay Time tpd(1) Max	7.5 ns
Voltage Supply - Internal	1.71V ~ 1.89V
Number of Logic Elements/Blocks	160
Number of Macrocells	128
Number of Gates	-
Number of I/O	79
Operating Temperature	0°C ~ 85°C (TJ)
Mounting Type	Surface Mount
Package / Case	100-TFBGA
Supplier Device Package	100-MBGA (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/intel/5m160zm100c5n

Recommended Operating Conditions

Table 3–2 lists recommended operating conditions for the MAX V device family.

Table 3–2. Recommended Operating Conditions for MAX V Devices

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCINT} *(1)*	1.8-V supply voltage for internal logic and in-system programming (ISP)	MAX V devices	1.71	1.89	V
V_{CCIO} *(1)*	Supply voltage for I/O buffers, 3.3-V operation	—	3.00	3.60	V
	Supply voltage for I/O buffers, 2.5-V operation	—	2.375	2.625	V
	Supply voltage for I/O buffers, 1.8-V operation	—	1.71	1.89	V
	Supply voltage for I/O buffers, 1.5-V operation	—	1.425	1.575	V
	Supply voltage for I/O buffers, 1.2-V operation	—	1.14	1.26	V
V_I	Input voltage	*(2)*, *(3)*, *(4)*	–0.5	4.0	V
V_O	Output voltage	—	0	V_{CCIO}	V
T_J	Operating junction temperature	Commercial range	0	85	°C
		Industrial range	–40	100	°C
		Extended range *(5)*	–40	125	°C

Notes to Table 3–2:

(1) MAX V device ISP and/or user flash memory (UFM) programming using JTAG or logic array is not guaranteed outside the recommended operating conditions (for example, if brown-out occurs in the system during a potential write/program sequence to the UFM, Altera recommends that you read back the UFM contents and verify it against the intended write data).

(2) The minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V for input currents less than 100 mA and periods shorter than 20 ns.

(3) During transitions, the inputs may overshoot to the voltages shown below based on the input duty cycle. The DC case is equivalent to 100% duty cycle. For more information about 5.0-V tolerance, refer to the *Using MAX V Devices in Multi-Voltage Systems* chapter.

V_{IN}	Max. Duty Cycle
4.0 V	100% (DC)
4.1 V	90%
4.2 V	50%
4.3 V	30%
4.4 V	17%
4.5 V	10%

(4) All pins, including the clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.

(5) For the extended temperature range of 100 to 125°C, MAX V UFM programming (erase/write) is only supported using the JTAG interface. UFM programming using the logic array interface is not guaranteed in this range.

Table 3–6. 3.3-V LVCMOS Specifications for MAX V Devices

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	3.0	3.6	V
V_{IH}	High-level input voltage	—	1.7	4.0	V
V_{IL}	Low-level input voltage	—	–0.5	0.8	V
V_{OH}	High-level output voltage	V_{CCIO} = 3.0, IOH = –0.1 mA *(1)*	V_{CCIO} – 0.2	—	V
V_{OL}	Low-level output voltage	V_{CCIO} = 3.0, IOL = 0.1 mA *(1)*	—	0.2	V

Note to Table 3–6:

(1) This specification is supported across all the programmable drive strength settings available for this I/O standard, as shown in the *MAX V Device Architecture* chapter.

Table 3–7. 2.5-V I/O Specifications for MAX V Devices

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	2.375	2.625	V
V_{IH}	High-level input voltage	—	1.7	4.0	V
V_{IL}	Low-level input voltage	—	–0.5	0.7	V
V_{OH}	High-level output voltage	IOH = –0.1 mA *(1)*	2.1	—	V
		IOH = –1 mA *(1)*	2.0	—	V
		IOH = –2 mA *(1)*	1.7	—	V
V_{OL}	Low-level output voltage	IOL = 0.1 mA *(1)*	—	0.2	V
		IOL = 1 mA *(1)*	—	0.4	V
		IOL = 2 mA *(1)*	—	0.7	V

Note to Table 3–7:

(1) This specification is supported across all the programmable drive strength settings available for this I/O standard, as shown in the *MAX V Device Architecture* chapter.

Table 3–8. 1.8-V I/O Specifications for MAX V Devices

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	1.71	1.89	V
V_{IH}	High-level input voltage	—	0.65 × V_{CCIO}	2.25 *(2)*	V
V_{IL}	Low-level input voltage	—	–0.3	0.35 × V_{CCIO}	V
V_{OH}	High-level output voltage	IOH = –2 mA *(1)*	V_{CCIO} – 0.45	—	V
V_{OL}	Low-level output voltage	IOL = 2 mA *(1)*	—	0.45	V

Notes to Table 3–8:

(1) This specification is supported across all the programmable drive strength settings available for this I/O standard, as shown in the *MAX V Device Architecture* chapter.

(2) This maximum V_{IH} reflects the JEDEC specification. The MAX V input buffer can tolerate a V_{IH} maximum of 4.0, as specified by the V_I parameter in Table 3–2 on page 3–2.

Preliminary and Final Timing

This section describes the performance, internal, external, and UFM timing specifications. All specifications are representative of the worst-case supply voltage and junction temperature conditions.

Timing models can have either preliminary or final status. The Quartus II software issues an informational message during the design compilation if the timing models are preliminary. Table 3–16 lists the status of the MAX V device timing models.

Preliminary status means the timing model is subject to change. Initially, timing numbers are created using simulation results, process data, and other known parameters. These tests are used to make the preliminary numbers as close to the actual timing parameters as possible.

Final timing numbers are based on actual device operation and testing. These numbers reflect the actual performance of the device under the worst-case voltage and junction temperature conditions.

Table 3–16. Timing Model Status for MAX V Devices

Device	Final
5M40Z	v
5M80Z	v
5M160Z	v
5M240Z	v
5M570Z	v
5M1270Z	v
5M2210Z	v

Performance

Table 3–17 lists the MAX V device performance for some common designs. All performance values were obtained with the Quartus II software compilation of megafunctions.

Table 3–17. Device Performance for MAX V Devices (Part 1 of 2)

Resource Used	Design Size and Function	Resources Used			Performance				Unit
					5M40Z/ 5M80Z/ 5M160Z/ 5M240Z/ 5M570Z		5M1270Z/ 5M2210Z		
		Mode	LEs	UFM Blocks	C4	C5, I5	C4	C5, I5	
LE	16-bit counter *(1)*	—	16	0	184.1	118.3	247.5	201.1	MHz
	64-bit counter *(1)*	—	64	0	83.2	80.5	154.8	125.8	MHz
	16-to-1 multiplexer	—	11	0	17.4	20.4	8.0	9.3	ns
	32-to-1 multiplexer	—	24	0	12.5	25.3	9.0	11.4	ns
	16-bit XORfunction	—	5	0	9.0	16.1	6.6	8.2	ns
	16-bit decoder with single address line	—	5	0	9.2	16.1	6.6	8.2	ns

Table 3–17. Device Performance for MAX V Devices (Part 2 of 2)

Resource Used	Design Size and Function	Resources Used			Performance				Unit
					5M40Z/ 5M80Z/ 5M160Z/ 5M240Z/ 5M570Z		5M1270Z/ 5M2210Z		
		Mode	LEs	UFM Blocks	C4	C5, I5	C4	C5, I5	
UFM	512 × 16	None	3	1	10.0	10.0	10.0	10.0	MHz
	512 × 16	SPI *(2)*	37	1	9.7	9.7	8.0	8.0	MHz
	512 × 8	Parallel *(3)*	73	1	*(4)*	*(4)*	*(4)*	*(4)*	MHz
	512 × 16	I^2C *(3)*	142	1	100 *(5)*	100 *(5)*	100 *(5)*	100 *(5)*	kHz

Notes to Table 3–17:

(1) This design is a binary loadable up counter.
(2) This design is configured for read-only operation in Extended mode. Read and write ability increases the number of logic elements (LEs) used.
(3) This design is configured for read-only operation. Read and write ability increases the number of LEs used.
(4) This design is asynchronous.
(5) The I^2C megafunction is verified in hardware up to 100-kHz serial clock line rate.

Internal Timing Parameters

Internal timing parameters are specified on a speed grade basis independent of device density. Table 3–18 through Table 3–25 on page 3–19 list the MAX V device internal timing microparameters for LEs, input / output elements (IOEs), UFM blocks, and MultiTrack interconnects.

f For more information about each internal timing microparameters symbol, refer to AN629: Understanding Timing in Altera CPLDs

Table 3–18. LE Internal Timing Microparameters for MAX V Devices (Part 1 of 2)

Symbol	Parameter	5M40Z/ 5M80Z/ 5M160Z/ 5M240Z/ 5M570Z				5M1270Z/ 5M2210Z				Unit
		C4		C5, I5		C4		C5, I5		
		Min	Max	Min	Max	Min	Max	Min	Max	
t_{LUT}	LE combinational look-up table (LUT) delay	—	1,215	—	2,247	—	742	—	914	ps
t_{COMB}	Combinational path delay	—	243	—	309	—	192	—	236	ps
t_{CLR}	LE register clear delay	401	—	545	—	309	—	381	—	ps
t_{PRE}	LE register preset delay	401	—	545	—	309	—	381	—	ps
t_{SU}	LE register setup time before clock	260	—	321	—	271	—	333	—	ps
t_H	LE register hold time after clock	0	—	0	—	0	—	0	—	ps
t_{CO}	LE register clock-to-output delay	—	380	—	494	—	305	—	376	ps0 — ococt713.1(p

Table 3–18. LE Internal Timing Microparameters for MAX V Devices (Part 2 of 2)

Symbol	Parameter	5M40Z/ 5M80Z/ 5M160Z/ 5M240Z/ 5M570Z				5M1270Z/ 5M2210Z				Unit
		C4		C5, I5		C4		C5, I5		
		Min	Max	Min	Max	Min	Max	Min	Max	
t_{CLKHL}	Minimum clock high or low time	253	—	339	—	216	—	266	—	ps
t_C	Register control delay	—	1,356	—	1,741	—	1,114	—	1,372	ps

Table 3–19. IOE Internal Timing Microparameters for MAX V Devices

Symbol	Parameter	5M40Z/ 5M80Z/ 5M160Z/ 5M240Z/ 5M570Z				5M1270Z/ 5M2210Z				Unit
		C4		C5, I5		C4		C5, I5		
		Min	Max	Min	Max	Min	Max	Min	Max	
t_{FASTIO}	Data output delay from adjacent LE to I/O block	—	170	—	428	—	207	—	254	ps
t_{IN}	I/O input pad and buffer delay	—	907	—	986	—	920	—	1,132	ps
t_{GLOB} *(1)*	I/O input pad and buffer delay used as global signal pin	—	2,261	—	3,322	—	1,974	—	2,430	ps
t_{IOE}	Internally generated output enable delay	—	530	—	1,410	—	374	—	460	ps
t_{DL}	Input routing delay	—	318	—	509	—	291	—	358	ps
t_{OD} *(2)*	Output delay buffer and pad delay	—	1,319	—	1,543	—	1,383	—	1,702	ps
t_{XZ} *(3)*	Output buffer disable delay	—	1,045	—	1,276	—	982	—	1,209	ps
t_{ZX} *(4)*	Output buffer enable delay	—	1,160	—	1,353	—	1,303	—	1,604	ps

Notes to Table 3–19:

(1) Delay numbers for t_{GLOB} differ for each device density and speed grade. The delay numbers for t_{GLOB}, shown in Table 3–19, are based on a 5M240Z device target.

(2) For more information about delay adders associated with different I/O standards, drive strengths, and slew rates, refer to Table 3–34 on page 3–24 and Table 3–35 on page 3–25.

(3) For more information about t_{XZ}

External Timing Parameters

External timing parameters are specified by device density and speed grade. All external I/O timing parameters shown are for the 3.3-V LVTTL I/O standard with the

Table 3–26lists the external I/O timing parameters for the 5M40Z, 5M80Z, 5M160Z, and 5M240Z devices.

Table 3–27

Table 3–30

External Timing I/O Delay Adders

The I/O delay timing parameters for the I/O standard input and output adders and the input delays are specified by speed grade, independent of device density.

Table 3–32 through Table 3–36 on page 3–25 list the adder delays associated with I/O pins for all packages. If you select an I/O standard other than 3.3-V LVTTL, add the input delay adder to the external t_{SU} timing parameters listed in Table 3–26 on page 3–20 through Table 3–31. If you select an I/O standard other than 3.3-V LVTTL with 16 mA drive strength and fast slew rate, add the output delay adder to the external t_{CO} and t_{PD} listed in Table 3–26 on page 3–20 through Table 3–31.

Table 3–35. External Timing Output Delay and Adders for Slow Slew Rate for MAX V Devices

I/O Standard		5M40Z/ 5M80Z/ 5M160Z/ 5M240Z/ 5M570Z				5M1270Z/ 5M2210Z				Unit
		C4		C5, I5		C4		C5, I5		
		Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	16 mA	—	5,913	—	6,043	—	6,612	—	6,293	ps
	8 mA	—	6,488	—	6,645	—	7,313	—	6,994	ps
3.3-V LVCMOS	8 mA	—	5,913	—	6,043	—	6,612	—	6,293	ps
	4 mA	—	6,488	—	6,645	—	7,313	—	6,994	ps
2.5-V LVTTL / LVCMOS	14 mA	—	9,088	—	9,222	—	10,021	—	9,702	ps
	7 mA	—	9,808	—	9,962	—	10,881	—	10,562	ps
1.8-V LVTTL / LVCMOS	6 mA	—	21,758	—	21,782	—	21,134	—	20,815	ps
	3 mA	—	23,028	—	23,032	—	22,399	—	22,080	ps
1.5-V LVCMOS	4 mA	—	39,068	—	39,032	—	34,499	—	34,180	ps
	2 mA	—	40,578	—	40,542	—	36,281	—	35,962	ps
1.2-V LVCMOS	3 mA	—	69,332	—	70,257	—	55,796	—	55,477	ps
3.3-V PCI	20 mA	—	6,488	—	6,645	—	339	—	418	ps